

## **PNP Epitaxial Silicon Transistor**

Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
I <sub>C</sub>	Collector Current	-150	mA	
P <sub>C</sub>	Collector Power Dissipation	100	mW	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Parameter Test Condition		Тур.	Max.	Units	
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-60	W W		V	
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10 <mark>mA. I<sub>B</sub>=0</mark>	-50			V	
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -10μΑ. I <sub>C</sub> =0	- 5			V	
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =60V, I <sub>E</sub> =0			-100	nA	
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-100	nA	
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -6V, I <sub>C</sub> = -1mA	40		700		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.18	-0.3	V	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -6V, I <sub>C</sub> = -1mA	-0.50	-0.62	-0.80	V	
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -6V, I <sub>C</sub> = -10mA	50	180		MHz	
Cob	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f=1MHz		2.8	170	pF	
NF	Noise Figure	V <sub>CE</sub> = -6V, I <sub>C</sub> = -0.3mA f=1MHz, Rs=10kΩ	2	6.0	N.OZ	dB	

### Thermal Characteristics T<sub>C</sub>=25°C unless otherwise noted

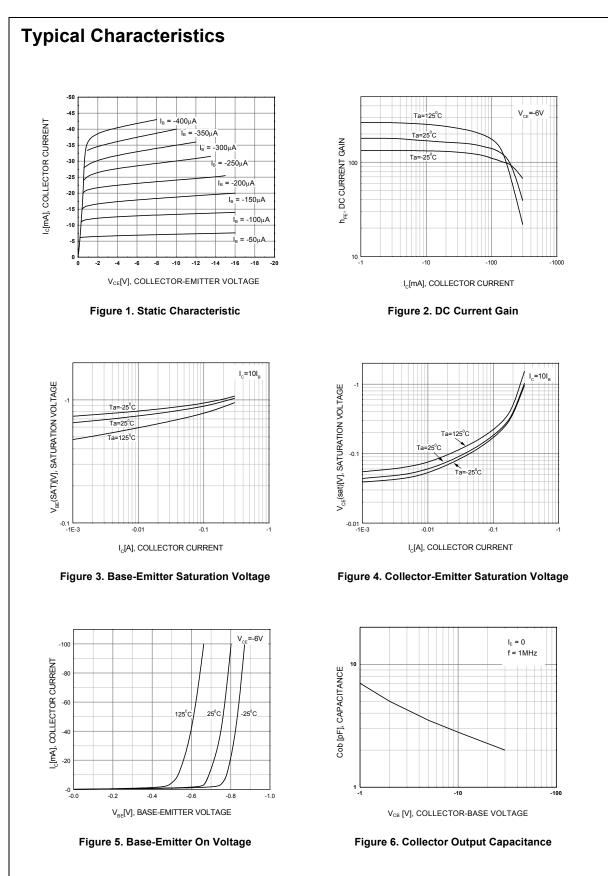
Symbol	Parameter	Max.	Units
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	1250	°C/W

## h<sub>FE</sub> Classification & Marking

Classification	R	0	Y	G	L
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700
Marking	A2	A3	A1	A4	A5







## FJZ733

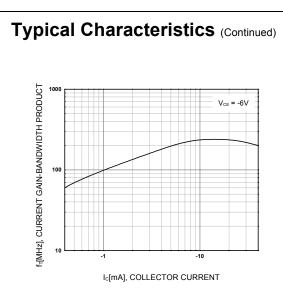
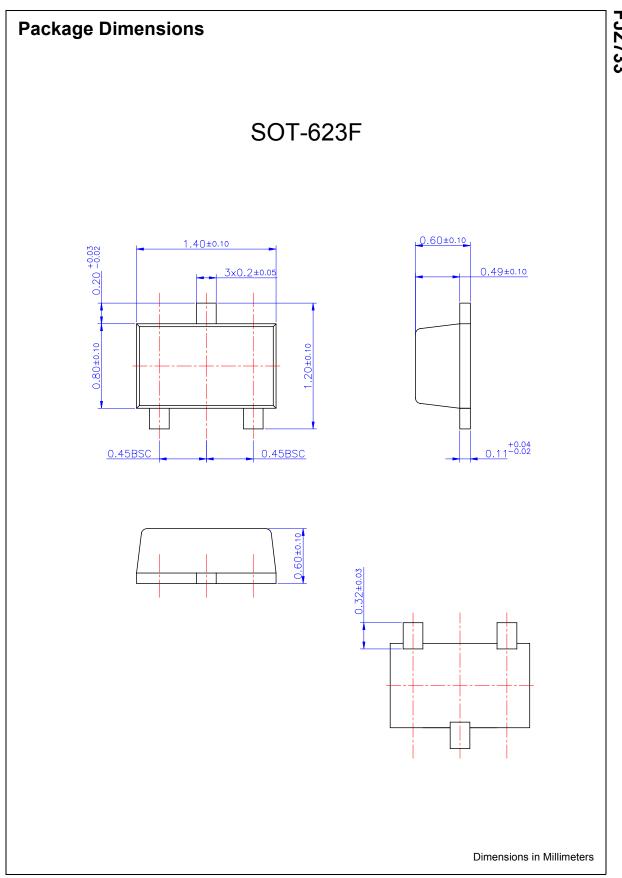


Figure 7. Current Gain Bandwidth Product

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